

IN THE CLAIMS:

Please amend claim 33 as follows:

33. (Amended) A process for depositing a tungsten silicide film on a substrate consisting essentially of:
depositing a discontinuous nucleation layer of tungsten silicide (WSi_x) on the substrate using a (CVD) process with a silane (SiH₄) silicon source gas and a reactant gas;
depositing a film of tungsten silicide (WSi_x) on the discontinuous nucleation layer using a (CVD) process by switching to dichlorosilane (SiH₂Cl₂) as a silicon source gas such that the dichlorosilane gas reacts with the reactant gas to form the tungsten silicide film; and
wherein said depositing said nucleation layerⁿ¹ of tungsten silicide and said depositing said film of tungsten silicide occur at a substantially equivalent temperature.